

Call for Papers

Special Section on Fundamentals and Applications of Advanced Semiconductor Devices

The IEICE (Institute of Electronics, Information and Communication Engineers) Transactions on Electronics announce a Special Section on "Fundamentals and Applications of Advanced Semiconductor Devices" to be published in **June 2019**. As digital processing units penetrate deeply into information society, the demand for high-performance semiconductor devices is kept growing. The purpose of this Special Section is to discuss various aspects of advanced semiconductor devices from fundamental physics to circuit applications. These include Si-based MOSFETs and bipolar transistors, compound semiconductor devices, and nano-scale devices.

1. Scope

Contributions are solicited in the following areas (but are not limited to these areas):

- Advanced integration technologies
- ULSI process technologies
- High-speed devices and circuits
- Power devices
- Wide bandgap materials and devices
- Novel devices and circuits
- Semiconductor devices applications
- MOS/bipolar devices technologies
- Compound semiconductor materials and devices
- Microwave/Millimeter-wave devices and circuits
- TFT materials, devices and circuits
- Quantum effect/single electron devices
- Characterization and simulation
- Sensors and displays

2. Submission Instructions

The deadline for submission is **September 25, 2018**. Types of manuscripts should be either "Paper (within 8 pages)" or "Brief Paper (within 4 pages)." Manuscripts should be prepared according to the "Information for Authors," the latest version of which is available at: http://www.ieice.org/eng/shiori/mokuji_es.html.

This special section will accept only papers by electronic submission. Prospective authors are requested to follow the submission procedure described below.

Submit a paper and transfer copyright of the paper using the IEICE Web site

https://review.ieice.org/regist/regist_baseinfo_e.aspx. Authors should choose the [Special-FU] *Fundamentals and Applications of Advanced Semiconductor Devices* as a "Issue/Section" on the online screen. Do not choose [Regular-EC].

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**At least one of the authors must be an IEICE member when the manuscript is submitted for review. Invited papers are an exception. We recommend authors to apply for the IEICE membership if they do not have one now. For membership applications, please visit the web-page, https://www.ieice.org/eng/join_ieice/index.html.*